Fast Hierarchical Optimization Method for High Speed Channel Design Using Channel Operating Margin (COM)

Spearker Bo Pu, (Samsung Electronics)

Paper Author

Bo Pu (Samsung Electronics), Rae Woon Yoo (Samsung Electronics) Jiyoung Park (Samsung Electronics) Jun So Pak (Samsung Electronics) Sungwook Moon (Samsung Electronics)





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SPEAKERS



Bo Pu

Senior Engineer, Samsung Electronics bob.pu@samsung.com / LinkedIn: Bo Pu

Senior engineer at Device Solution division (Semiconductor), Samsung Electronics, Hwaseong, Korea.

He is responsible for driving signal/power integrity design and analysis as well as design methodology development for high speed serial and memory interfaces up to multiple Gbps. His research interests include modeling, design, and analysis of chip-package-PCB systems for signal/power integrity, and electromagnetic Compatibility (EMC).

He received the B.S. in electrical engineering from the Harbin Institute of Technology, China, in 2009, and combined M.S. & Ph.D. in electrical and electronics engineering from Sungkyunkwan University, Korea, in 2015.

Dr. Pu received the Best Student Paper Award at the IEEE APEMC in 2011 and a Young Scientists Award from the International Union of Radio Science in 2014. He served as the session chair of IEEE APEMC 2017 and is a TPC member of Joint IEEE EMC symposium and APEMC 2018.





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Outline

- Motivation and Introduction;
- An Overview of Channel Operating Margin (COM);
- Conventional Optimization Method by COM;
- Proposed Design Flow based on our Hierarchical Optimization Method;
- Design Strategy of Via in High Speed Channel;
- Channel Operating Margin Analysis for Designed Channel;
- Conclusion and Future Plan.





Motivation



[Reference] High-Speed I/O Speed Roadmap, International Technology Roadmap for Semiconductors (ITRS)



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Motivation

 Diverse and complicate criteria in both time and frequency domains are used to estimate the performance of channel for high speed signal propagation.





Definition of 56G Channel

 Definition of the high speed channel applications by OIF CEI-56G.

Scenarios	Interface	Distance	Maximum Loss	Modulation
Chip to OE	CEI-56G-USR	<1 cm	2 dB@ 28GHz	NRZ
Chip to nearby OE	CEI-56G-XSR	<5 cm	6 dB@ 28GHz	NRZ or PAM4
Chip to Module	CEI-56G-VSR	<10 cm	10 dB@ 14GHz 23 dB@ 28GHz	NRZ or PAM4
Chip to Chip	CEI-56G-MR	<50 cm	20 dB@ 14GHz 47 dB@ 28GHz	PAM4
Backplane	CEI-56G-LR	<100 cm	35 dB@ 14GHz 64.5-94 dB@ 28GHz	PAM4



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- [Ref] OIF CEI-56G Common Electrical, OIF document number: OIF2014.380.02, 2015.
- [Ref] Geoff Zhang, Hongtao Zhang, Santiago Asuncion, and Brandon Jiao, "A Tutorial on PAM4 Signaling for 56G Serial Link Applications", DesignCon 2017, Santa Clara, CA, 2017.





Introduction

- An Overview of Channel Operating Margin Schematic.
- COM has been proposed as a figure of merit to evaluate the quality of channel.



[Ref] IEEE Std 802.3bj-2014 IEEE Standard for Ethernet Amendment 2: Physical Layer Specifications and Management Parameters for 100 Gb/s Operation Over Backplanes and Copper Cables.



Introduction

The computation process for channel operating margin.



Introduction

Can COM be used as a deign guide in the design stage, not the evaluation period?



Conventional Channel Design Methods

- One factor at a time (OFAT) experiment
- Cons: It cannot consider the <u>mutual effects</u> between factors.
- Design of Experiments + Response Surface Method
- Pros: Can include the interaction between factors;
- Cons: <u>Huge time cost</u> for the interaction with large factors;
- Design of Experiments + Artificial Neural Networks
- Pros: Can *handle the insufficient accuracy* of RSM for non-linear and higher order responses (An appropriate approach for channel design based on previous data)
- Cons: <u>Requires large enough data to train the ANN</u> to ensure accuracy (Not possible in the early design stage)





Fig. A typical structure for ANN.



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- Design Flow based on proposed Fast hierarchical optimization COM method.
- ✓ TAT Reduction
- Hierarchical structure
- Electrical to Physical Characteristics
- ✓ Realistic Scenario
- Interaction among factors
- ✓ High Accuracy
- Channel Sim. + 2.5D/3D



Determine physical factors by 2.5D/3D full wave analysis based on optimized impedance



✤ Components in a typical 56G LR Channel

- Silicon Range
- Transmitter and receiver
- Material & Stack up
- Conductive and dielectric
- PCB, Package and Connector
- Transmission line Microstrip and Stripline
- Via and ball discontinuity
- Cable connector
- Discrete device AC capacitor, etc.



Fig. Configuration of long reach channel defined by OIE-CEI.



Conventional DoE for Channel Design

- ***** The most common DoE for channel design is a horizontal algorithm by physical geometry:
- Consider all physical parameters at the same level.
- To extract the best case by burden iterations.

РКС	ine ard Simu	Conn.	Backp	lane ed by Conve	Conn. ntional DO	Line Card	РКС
	Via_layerA	Trace_layer A	Via_layerB	Trace_layerB	Connector_ layerC	Via_layerC	Trace_layerC
Variables (Physical Parameters)	2 (Pad & Antipad)	2 (Trace Width & gap of diff. lines)	2 (Pad & Antipad)	2 (Trace Width & gap of diff. lines)	1 (Impedance)	2 (Pad & Antipad)	2 (Trace Width & gap of diff. lines)
Sweep variables in a ±10% range (At least 5 set-5% as step to ensure accuracy)	10	10	10	10	10	10	10
Total Simulation Times:				2 ⁶ * 10 ⁷	6		



• Step1: The optimization starts on the top level with <u>three layers of the channel.</u>

(line card layer A, backplane layer C and line card layer B)

Simplification



Layer_A Layer_B Layer_C Layer_C Layer_C Layer_C Layer_B Layer_C Layer_B Layer_C Layer_B Layer_C Layer_

 Single <u>Electrical</u> Characteristic

 Physical → Electrical
 (Representative Value containing diverse physical factors)

Z Impedance

- Establishment of channel model by layer
- Determined the optimized total impedance for layer_A, layer_B and layer_C.
- Layer_A&B: Line card
- Layer_C: Backplane
- Terminations: Tx and Rx



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After Performing COM

 Step2: Expanded each layer to corresponding components and determine the optimized impedance for each device by COM computation.





- Step 3: 2.5D or 3D simulator used to extract the precise geometry for complex structure
- Handling Inhomogeneous configurations in Z-axis: Via, Connector
- Accuracy guaranteed: 2.5D or 3D full-wave simulator
- **Step 4: Perform COM with the obtained alternative parameters and determine the best one.**
- Consider the bias of physical factors due to process in fabrication for alternative parameters





- Determined the physical parameters based on optimized impedance using 2.5D and 3D simulator
- Channel Completion and analysis to get best COM.







Iterations cost in our proposed design flow with a hierarchical optimization method.

	Layer_A	Layer_B	Layer_C	Variables	2	2	3	
Variables	1	1	1	Sweep variables in a	10	10	10	
Sweep variables in a ±10% range	10	10	10	Total Simulation Times:	12	12* 10 ³ =12000		
Total Simulation Times:	1	² * 10 ³ =100	00		夺			
Determined tl	he optimiz	ed total in	npedance	Variables	2	2	2	
 for layer_A, layer_B and layer_C. Determined the optimized impedance for 			Physical Parameters	2	2	2		

Proposed Fast Hierarchical Optimization Method

- each component in every layer_A&B&C.
- Determined the physical parameters based • on optimized impedance using 2.5D and **3D simulator**





Comparison for Conventional and Proposed Methods

- Time: A amazing time reduction is realized by the proposed methods.
- Accuracy: Higher accuracy gets ensured.

Opt. method	Conventional (Physical Parameters based)	Proposed (Hierarchy)
Loop Sweeping	2 ⁶ * 10 ⁷	13064
Estimated Time Cost (Avg. 5 min. for each COM calculation of 56G)	74074 Months	1.512 Months
TAT reduction	(1-1.512/7407	4) *100% = 99.9979%
Accuracy	Normal (2D Channel Designer)	High (Enhanced by 2.5D/3D simulator)





- Via is the most common discontinuity in a passive channel, and a stable impedance transition is demanded at Via area.
- Amateur design of the discontinuity Via may cause disaster for high speed channel with multiple Gbp data rate.
- The basic factors of a typical via are via barrel, via pad and anti-pad.





- Parasitic of Via to affect the stabilization of impedance.
- <u>Inductive effect</u> generating positive fluctuation: loop by via barrel and a return path.
- Capacitive effect generating negative fluctuation: coupling between pad and nearby ground.





- Proposed strategy to mitigate the variance on impedance
- Transition coupled area: working as capacitance compensation
- Defected ground structure: to handle the redundant vertical capacitance.





Expected stable impedance by implementing the design guide of via.





COM Analysis for Designed Channel

- Two channels (Ball to Ball, without Package) with different insertion loss and crosstalk levels are design to demonstrate the effect of loss and crosstalk on the channel operating margin.
- Channel 1 has more insertion loss at Nyquist frequency of 14GHz but less power sum RMS value for crosstalk
- channel 2 is designed with a less insertion loss to channel1 but with a worse condition of crosstalk.





COM Analysis for Designed Channel

- Effect on COM by the addition of package
- Does the package model defined in IEEE 802.3 COM need to be updated?
- Conditions of two above mentioned channels (*Bump to Bump, with real designed package*)
- IEEE pre-defined package (IEEE 802.3bj)
- Real designed package (Figure below)



COM Analysis for Designed Channel

- **Crosstalk of package also generates a influence on the COM.**
- A difference is observed between the <u>IEEE pre-defined package (w/o Xtalk)</u> and <u>real package (w/ Xtalk)</u>, although there is the similar level for loss.

Parameter	Definition	Setting	Units	
C_d	Single-ended device capacitance	[1.8e-4 1.8e-4]	nF	
z_p select	Test cases of package model	[12]	Test case	
z_p (TX)	Victim transmitter package trace lengths	[12 30]	mm	
z p (NEXT)	NEXT aggressor transmitter package trace	[12 12]	mm	
	lengths			
z p (FEXT)	FEXT aggressor transmitter package trace	[12 30]	mm	
	lengths	[]		
z_p (RX)	Victim receiver package trace lengths	[12 30]	mm	
Ср	Single-ended package-to-board capacitance	[1.1e-4 1.1e-4]	nF	
R_0	Reference single-ended impedance	50	Ohm	
R_d	Single-ended termination resistance	[55 55]	Ohm	

Table 1: Definition of parameters for the package model used in COM extraction.

Table 2: Comparison of COM for channels with diverse package conditions.

Cases	Package Condition	COM (dB)
Channel 1	Without package	5.7470
	With IEEE pre-defined package	3.9445
	With real package	3.5176
Channel 2	Without package	4.5540
	With IEEE pre-defined package	3.5175
	With real package	3.4785



Conclusion and Future Plan

- In this paper, we first propose a design flow for channel design by a fast hierarchical optimization method based on COM.
- Advantages on accuracy and speed for our proposed hierarchical design flow was demonstrated.
- Novel design strategy to mitigate the fluctuation of impedance at via was addressed
- Characteristic such as loss and crosstalk of the designed channel is demonstrated.
- The effect of package on the COM was discussed by a comparison of diverse package conditions.
- In future works, we will concentrated on the enhancement of the design flow and contribute to the accurate COM criterion for high speed links.





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Thank you!

Bo Pu bob.pu@samsung.com

QUESTIONS?



